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MEG-03-005

May 21, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/796,427 03/09/04 |
Mou-Shiung Lin et al.
POST-PASSIVATION METAL SCHEME ON
AN IC CHIP WITH COPPER
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 24, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 5/24/04

MEG-03-005

U.S. Patent Application MS-002CCC_CIP, filed 05/24/02, Serial No. 10/154,662, assigned to the same assignee, "Top Layers of Metal for High Performance IC's," discusses the manufacturing of high performance Integrated Circuit (IC's).

U.S. Patent Application MEG-02-016, filed 05/27/03, Serial No. 10/445,558, assigned to the same assignee, "High Performance System-on-Chip Inductor Using Post Passivation," discusses the manufacturing of high performance IC's.

U.S. Patent Application Publication US 2004/0029404 A1 to Lin, "High Performance System-on-Chip Passive Device Using Post Passivation Process," discloses a system and method for forming post passivation passive components, such as resistors and capacitors.

U.S. Patent Application Publication US 2004/0016948 A1 to Lin, "High Performance System-on-Chip Discrete Components Using Post Passivation Process," discloses a system and method for forming post passivation discrete components.

U.S. Patent 6,544,880 to Akram, "Method of Improving Copper Interconnects of Semiconductor Devices for Bonding," discloses gold over a copper pad and optionally additional metals to prevent formation of intermetallic compounds in wire bonding.

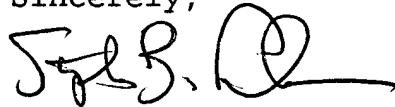
The following two U.S. Patents teach using an Al cap over a copper bond pad for wire bonding:

- 1) U.S. Patent 6,451,681 to Greer, "Method of Forming Copper Interconnection Utilizing Aluminum Capping Film".
- 2) U.S. Patent 6,376,353 to Zhou et al., "Aluminum and Copper Bimetallic Bond Pad Scheme for Copper Damascene Interconnects."

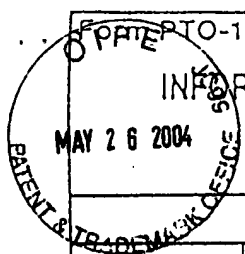
The following two U.S. Patents discloses a post-passivation interconnection process:

- 1) U.S. Patent 6,495,442 to Lin et al., "Post Passivation Interconnection Schemes on Top of the IC Chips."
- 2) U.S. Patent 6,383,916 to Lin, "Top Layers of METal for High Performance IC's."

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761



INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
(Use several sheets if necessary)

Docket Number (Optional)	Application Number
MEG-03-005	10/796,427
Applicant Mou-Shiung Lin et al.	
Filing Date 03/09/04	Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6544880	4/8/03	Akram	438	617	6/14/99
	6451681	9/17/02	Greer	438	601	10/4/99
	6376353	4/23/02	Zhou et al.	438	612	7/3/00
	6495442	12/17/02	Lin et al.	438	618	10/18/00
	6383916	5/7/02	Lin	438	637	2/17/99

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

-	US Patent App. MSL-98-002 CCC CIP, Filed 05/24/02, Ser # 10/154,662, assigned to the same assignee, "Top Layers of Metal for High Performance IC's".
-	US Patent App. MEG-02-016, Filed 05/27/03, Ser. # 10/445,558, "High Performance System-on-Chip Inductor Using Post Passivation Process".

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Doctor Number (Optional)

MEG-03-005

Application Number

10796.427

Applicant:

Applicant: Mou-Shiung Lin et al.

Filing Date

Filing Date 03/09/04

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

-	U.S. Patent App. Pub. US 2004/0029404 A1 to Lin, Pub. Date 2/12/04, Filed 5/27/03, US Cl. 438/958.
-	U.S. Patent App. Pub. US 2004/0016948 A1 to Lin, Pub. Date 1/29/04, Filed 5/27/03, US Cl. 257,300.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.